

#### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON) max</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
-20V	1.0Ω @ V <sub>GS</sub> = -4.5V	-600mA
	1.5Ω @ V <sub>GS</sub> = -2.5V	-500mA
	2.0Ω @ V <sub>GS</sub> = -1.8V	-400mA
	3.0Ω @ V <sub>GS</sub> = -1.5V	-250mA

### **Description**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

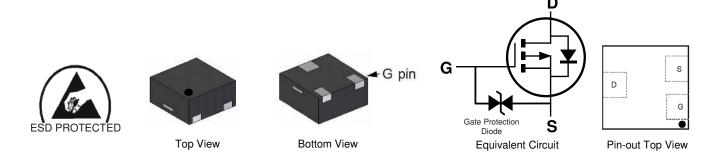
- DC-DC Converters
- Power Management Functions

## **Features**

- Low On-Resistance
- Very Low Gate Threshold Voltage V<sub>GS(TH)</sub>, -1.0V Max
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

- Case: X1-DFN1212-3
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)



#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP21D6UFD-7	X1-DFN1212-3	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# **Marking Information**

P16 YM ● P16 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

Date Code Key

Date Code Hoj												
Year	2017	2018	20	19	2020	2021	2022	2023	20	24	2025	2026
Code	E	F	(	G	Н	I	J	K		L	М	N
									_			
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	±8	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	I <sub>D</sub>	-600 -500	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-2	Α
Maximum Body Diode Continuous Current	Is	-800	mA

### **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		$P_{D}$	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	280	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	0.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	140	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V$ , $I_D = -1mA$		
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>		_	-100	nA	$V_{DS} = -20V, V_{GS} = 0V$		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.5	_	-1.0	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$		
			0.7	1.0		$V_{GS} = -4.5V$ , $I_D = -100mA$		
			0.9	1.5		$V_{GS} = -2.5V, I_D = -80mA$		
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	1	1.2	2.0	Ω	$V_{GS} = -1.8V, I_D = -40mA$		
			1.5	3.0		$V_{GS} = -1.5V, I_D = -30mA$		
		_	5	_		$V_{GS} = -1.2V, I_{D} = -1mA$		
Diode Forward Voltage	$V_{SD}$	_	-0.75	-1.2	V	$V_{GS} = 0V, I_{S} = -330mA$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C <sub>iss</sub>	1	46.1	_		.,		
Output Capacitance	Coss	1	7.2	_	pF	$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz		
Reverse Transfer Capacitance	C <sub>rss</sub>		4.9	_		1 – 1.01011 12		
Total Gate Charge V <sub>GS</sub> = -4.5V	$Q_g$	_	0.5	_				
Total Gate Charge V <sub>GS</sub> = -8V	Qg	_	0.8	_	nC	10)/ 1 050 1		
Gate-Source Charge	Q <sub>gs</sub>	_	0.1	_	IIC	$V_{DS} = -10V, I_D = -250mA$		
Gate-Drain Charge	Q <sub>qd</sub>	_	0.1	_				
Turn-On Delay Time	t <sub>D(ON)</sub>	_	8.5	_		V 0V V 0.5V		
Turn-On Rise Time	t <sub>R</sub>		4.3	_		$V_{DD} = -3V, V_{GS} = -2.5V,$		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	20.2	_	ns	$R_L = 300\Omega, R_G = 25\Omega,$		
Turn-Off Fall Time	t <sub>F</sub>	_	19.2	_		I <sub>D</sub> = -100mA		

Notes:

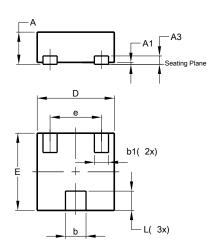
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to product testing.



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X1-DFN1212-3

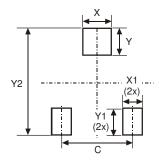


X1-DFN1212-3						
Dim	Min	Max	Тур			
Α	0.47	0.53	0.50			
A1	0	0.05	0.02			
A3	-	-	0.13			
b	0.27	0.37	0.32			
b1	0.17	0.27	0.22			
D	1.15	1.25	1.20			
Е	1.15	1.25	1.20			
е	-	-	0.80			
Ĺ	0.25	0.35	0.30			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X1-DFN1212-3



Dimensions	Value (in mm)
С	0.80
Х	0.42
X1	0.32
Υ	0.50
Y1	0.50
Y2	1.50



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